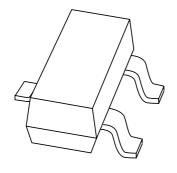
## **DISCRETE SEMICONDUCTORS**

## DATA SHEET



# PMBT2907; PMBT2907A PNP switching transistors

Product data sheet Supersedes data of 1999 Apr 27 2004 Jan 16



## **PNP** switching transistors

PMBT2907; PMBT2907A

#### **FEATURES**

- High current (max. 600 mA)
- Low voltage (max. 60 V).

#### **APPLICATIONS**

• Switching and linear amplification.

#### **DESCRIPTION**

PNP switching transistor in a SOT23 plastic package. NPN complements: PMBT2222 and PMBT2222A.

#### **MARKING**

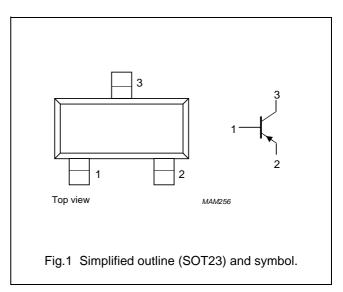
TYPE NUMBER	MARKING CODE <sup>(1)</sup>
PMBT2907	*2B
PMBT2907A	*2F

#### Note

- 1. \* = p : Made in Hong Kong.
  - \* = t : Made in Malaysia.
  - \* = W: Made in China.

#### **PINNING**

PIN	DESCRIPTION
1	base
2	emitter
3	collector



#### **ORDERING INFORMATION**

TYPE	PACKAGE		
NUMBER	NAME	DESCRIPTION	VERSION
PMBT2907	-	plastic surface mounted package; 3 leads	SOT23
PMBT2907A	_	plastic surface mounted package; 3 leads	SOT23

## PNP switching transistors

PMBT2907; PMBT2907A

#### **LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V <sub>CBO</sub>	collector-base voltage	open emitter	_	-60	V
$V_{CEO}$	collector-emitter voltage	open base			
	PMBT2907		_	-40	V
	PMBT2907A		_	-60	V
V <sub>EBO</sub>	emitter-base voltage	open collector	_	<b>-</b> 5	V
I <sub>C</sub>	collector current (DC)		_	-600	mA
I <sub>CM</sub>	peak collector current		_	-800	mA
I <sub>BM</sub>	peak base current		_	-200	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	_	250	mW
T <sub>stg</sub>	storage temperature		-65	+150	°C
Tj	junction temperature		_	150	°C
T <sub>amb</sub>	operating ambient temperature		-65	+150	°C

#### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	note 1	500	K/W

#### Note

1. Transistor mounted on an FR4 printed-circuit board.

## PNP switching transistors

## PMBT2907; PMBT2907A

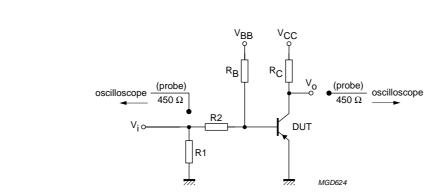
#### **CHARACTERISTICS**

 $T_i = 25$  °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I <sub>CBO</sub>	collector-base cut-off current	I <sub>E</sub> = 0; V <sub>CB</sub> = -50 V			
	PMBT2907		_	-20	nA
	PMBT2907A		_	-10	nA
	collector-base cut-off current	$I_E = 0$ ; $V_{CB} = -50 \text{ V}$ ; $T_j = 125 ^{\circ}\text{C}$			
	PMBT2907		_	-20	μΑ
	PMBT2907A		_	-10	μΑ
I <sub>EBO</sub>	emitter-base cut-off current	$I_C = 0; V_{EB} = -5 \text{ V}$	_	-50	nA
h <sub>FE</sub>	DC current gain	$I_C = -0.1 \text{ mA}; V_{CE} = -10 \text{ V}$			
	PMBT2907		35	_	
	PMBT2907A		75	_	
	DC current gain	$I_C = -1 \text{ mA}; V_{CE} = -10 \text{ V}$			
	PMBT2907		50	_	
	PMBT2907A		100	_	
	DC current gain	$I_C = -10 \text{ mA}; V_{CE} = -10 \text{ V}$			
	PMBT2907		75	_	
	PMBT2907A		100	_	
	DC current gain	$I_C = -150 \text{ mA}; V_{CE} = -10 \text{ V}$	100	300	
	DC current gain	$I_C = -500 \text{ mA}; V_{CE} = -10 \text{ V}$			
	PMBT2907		30	_	
	PMBT2907A		50	_	
V <sub>CEsat</sub>	collector-emitter saturation	$I_C = -150 \text{ mA}; I_B = -15 \text{ mA}$	_	-400	mV
	voltage	$I_C = -500 \text{ mA}; I_B = -50 \text{ mA}$	_	-1.6	V
V <sub>BEsat</sub>	base-emitter saturation voltage	$I_C = -150 \text{ mA}; I_B = -15 \text{ mA}$	_	-1.3	V
		$I_C = -500 \text{ mA}; I_B = -50 \text{ mA}$	_	-2.6	V
C <sub>c</sub>	collector capacitance	$I_E = I_e = 0$ ; $V_{CB} = -10 \text{ V}$ ; $f = 1 \text{ MHz}$	_	8	pF
C <sub>e</sub>	emitter capacitance	$I_C = I_c = 0$ ; $V_{EB} = -2 \text{ V}$ ; $f = 1 \text{ MHz}$	_	30	pF
f <sub>T</sub>	transition frequency	$I_C = -50 \text{ mA}; V_{CE} = -20 \text{ V}; f = 100 \text{ MHz}$	200	_	MHz
Switching t	imes (between 10% and 90% leve	els); (see Fig.2)			
t <sub>on</sub>	turn-on time	$I_{Con} = -150 \text{ mA}; I_{Bon} = -15 \text{ mA};$	_	40	ns
t <sub>d</sub>	delay time	I <sub>Boff</sub> = 15 mA	_	12	ns
t <sub>r</sub>	rise time		_	30	ns
t <sub>off</sub>	turn-off time		_	365	ns
ts	storage time		_	300	ns
t <sub>f</sub>	fall time		_	65	ns

## PNP switching transistors

## PMBT2907; PMBT2907A



$$\begin{split} &V_i = -9.5 \; V; \, T = 500 \; \mu s; \; t_p = 10 \; \mu s; \; t_r = t_f \leq 3 \; ns. \\ &R1 = 68 \; \Omega; \; R2 = 325 \; \Omega; \; R_B = 325 \; \Omega; \; R_C = 160 \; \Omega. \\ &V_{BB} = 3.5 \; V; \; V_{CC} = -29.5 \; V. \\ &Oscilloscope: input impedance \; Z_i = 50 \; \Omega. \end{split}$$

Fig.2 Test circuit for switching times.

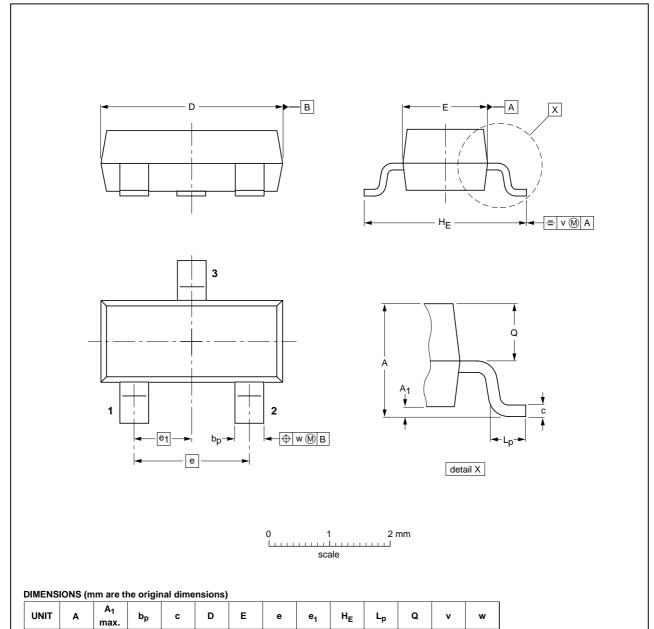
## PNP switching transistors

## PMBT2907; PMBT2907A

#### **PACKAGE OUTLINE**

#### Plastic surface-mounted package; 3 leads

SOT23



OUTLINE	REFERENCES			EUROPEAN	ICCUE DATE	
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
SOT23		TO-236AB				<del>-04-11-04</del> 06-03-16

1.9

0.45

0.55

0.1

2004 Jan 16 6

0.48

0.38

0.9

### PNP switching transistors

PMBT2907; PMBT2907A

#### **DATA SHEET STATUS**

DOCUMENT STATUS <sup>(1)</sup>	PRODUCT STATUS <sup>(2)</sup>	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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#### **Customer notification**

This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content, except for package outline drawings which were updated to the latest version.

#### **Contact information**

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Printed in The Netherlands R75/05/pp8 Date of release: 2004 Jan 16 Document order number: 9397 750 12459

